

Title (en)

METHOD FOR PRODUCING A SILICIUM CAPACITOR

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES SILIZIUMKONDENSATORS

Title (fr)

PROCEDE DE PRODUCTION D'UN CONDENSATEUR AU SILICIUM

Publication

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Application

EP 98905245 A 19980112

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Abstract (en)

[origin: DE19701935C1] The invention relates to method for producing a silicium capacitor by producing hole structures (2) on a silicium substrate (1). A conductive area (3) is produced in the surface of said structures by doping, to which a dielectric layer (4) and a conducting layer (5) is applied without filling the hole structures (2). In order to compensate the mechanical stress of the silicium substrate (1) caused by the doping of the conductive area (3), a conformal auxiliary layer (6) is formed on the surface of the conducting layer (5), which is subjected to compressive mechanical tension

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